

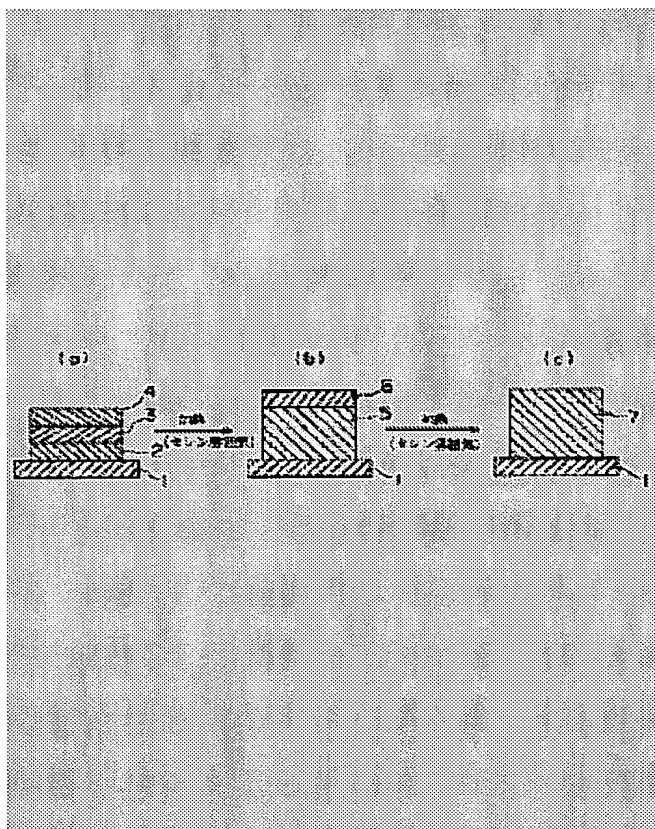
SEMICONDUCTOR THIN FILM WITH CIS-BASED CHALCOPYRITE, STRUCTURE, SOLAR BATTERY, WITH THE THIN FILM AND THEIR MANUFACTURE

Patent number: JP11274526
Publication date: 1999-10-08
Inventor: IKETANI TAKESHI; KAMIYA TAKESHI
Applicant: YAZAKI CORP
Classification:
- international: H01L31/04
- european:
Application number: JP19980074229 19980323
Priority number(s): JP19980074229 19980323

[Report a data error here](#)

Abstract of JP11274526

PROBLEM TO BE SOLVED: To provide a graded band gap structure with good repeatability at low cost. **SOLUTION:** In a semiconductor thin film with a CIS-based chalcopyrite structure, with a large band gap energy at a position near (4) a substrate 1, and a small band gap at a position near a film surface put in contact with an n-type semiconductor. In this case, the composition of Al and In is changed sequentially in a way that an atom number ratio of $Al/(In+Al)$ near the substrate 1 is smaller than that of $Al/(In+Al)$ on the film surface.



Data supplied from the **esp@cenet** database - Worldwide